L	Hits	Search Text	DB	Time stamp
Number				-
1	3	365/158,243,163,113,105,96,103,104,175.ccl		2004/09/17
		and high-resistance same low-resistance	US-PGPUB;	11:20
		same heat	EPO; JPO;	
]			DERWENT;	
] _			IBM_TDB	
6	305		USPAT;	2004/09/17
		cel1\$3	US-PGPUB;	11:55
1			EPO; JPO;	
			DERWENT; IBM TDB	
7	100	365/158,175,113,163,171,189.03,177,105,148		c2:010s4/09/17
'	100	and (heat\$3 or thermal) near5 cell\$3	US-PGPUB;	11:57
		and (neaty) of enermaly nears eerrys	EPO; JPO;	11.57
			DERWENT;	
			IBM TDB	
8	26	365/158,175,113,163,171,189.03,177,105,148	_	c2d0s4/09/17
		and (heat\$3 or thermal) near5 cell\$3 and	US-PGPUB;	11:57
1		transistor\$1 and diode	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
9	26			
		and (heat\$3 or thermal) near5 cell\$3 and	US-PGPUB;	11:58
		\$8transistor and diode	EPO; JPO;	
			DERWENT;	
	101	high-registance same low wasistance same	IBM_TDB USPAT;	2004/09/17
_	101	high-resistance same low-resistance same heat	US-PGPUB;	11:20
		Neac	EPO; JPO;	11.20
			DERWENT;	
			IBM TDB	
_	4	365/\$.ccls. and high-resistance same	USPAT;	2004/09/04
	_	low-resistance same heat	US-PGPUB;	11:37
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	4	("4177475" "4203123" "4499557"	USPAT	2004/09/04
		"4531144").PN.	******	11:33
-	1	high-resistance same low-resistance same	USPAT;	2004/09/04
		heat same switch\$3 same transistor	US-PGPUB; EPO; JPO;	11:39
			DERWENT;	
			IBM TDB	
_	10	high-resistance same low-resistance same	USPAT;	2004/09/04
		heat same switch\$3	US-PGPUB;	11:56
	İ		EPO; JPO;	
	1		DERWENT;	
	-		IBM_TDB	
-	5	`	USPAT	2004/09/04
		"3624354" "3982092").PN.		11:42
-	333	(heat with rate) same transistor	USPAT;	2004/09/17
			US-PGPUB;	11:36
			EPO; JPO; DERWENT;	
			IBM TDB	
_	3	365/\$.ccls. and (heat with rate) same	USPAT;	2004/09/04
	1	transistor	US-PGPUB;	11:59
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	("5119329" "5506748").PN.	USPĀT	2004/09/04
				11:58
-	73	(heat with rate) same switch\$3 same	USPAT;	2004/09/04
		transistor	US-PGPUB;	11:59
			EPO; JPO;	
	1		DERWENT;	
			IBM TDB	

	627		TIG D D M	2004/00/07
-	637	ovonic	USPAT; US-PGPUB;	2004/09/07 08:36
İ			EPO; JPO;	00.30
			DERWENT;	
			IBM_TDB	
-	1	ovonic same (heat\$3 with rate\$1)	USPAT;	2004/09/07
			US-PGPUB;	07:37
			EPO; JPO; DERWENT;	
			IBM TDB	
_	40	ovonic same heat\$3	USPAT;	2004/09/07
			US-PGPUB;	08:09
			EPO; JPO;	
			DERWENT;	
	1.5		IBM_TDB	2004/00/07
-	15	ovonic same transistor	USPAT; US-PGPUB;	2004/09/07
			EPO; JPO;	00.10
!			DERWENT;	
1			IBM TDB	
_	77	365/\$.ccls. and ovonic	USPĀT;	2004/09/07
			US-PGPUB;	08:36
			EPO; JPO;	
			DERWENT; IBM TDB	
_	60	365/\$.ccls. and ovonic and transistor	USPAT;	2004/09/07
		boo, y. cold. and overlie and chambleton	US-PGPUB;	10:08
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	8		USPAT;	2004/09/07
		near4 heat\$3	US-PGPUB; EPO; JPO;	10:17
	}		DERWENT;	
			IBM TDB	
_	32	365/\$.ccls. and ovonic and transistor and	USPAT;	2004/09/07
		heat\$3	US-PGPUB;	10:43
			EPO; JPO;	
			DERWENT;	
	60	365/\$.ccls. and ovonic and transistor	IBM_TDB USPAT;	2004/09/07
	""	303/7.ccis. and ovonic and cransistor	US-PGPUB;	12:13
			EPO; JPO;	
!			DERWENT;	
			IBM_TDB	0004/00/07
-	19	365/\$.ccls. and ovonic and (transistor	USPAT;	2004/09/07
		with array\$1)	US-PGPUB; EPO; JPO;	12:23
1			DERWENT;	
	1		IBM TDB	
-	2	("5363329" "5920788").PN.	USPĀT	2004/09/07
	1	[,		12:15
-	2	1 ' ' '	USPAT;	2004/09/07
	1	(transistor with array\$1)	US-PGPUB; EPO; JPO;	12:24
	1		DERWENT;	
			IBM TDB	
-	19	365/\$.ccls. and (ovonic or	USPAT;	2004/09/07
		phase-changeable) and (transistor with	US-PGPUB;	12:25
		array\$1)	EPO; JPO;	
•			DERWENT;	
_	8	365/\$.ccls. and (ovonic or	IBM_TDB USPAT;	2004/09/07
	"	phase-changeable) and (transistor with	US-PGPUB;	12:26
	1	array\$1) and heat\$3	EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
-	12	1 ,	USPAT;	2004/09/07
		(transistor with array\$1) and heat\$3	US-PGPUB; EPO; JPO;	12:47
			DERWENT;	
			IBM TDB	
	1	<u> </u>		<u> </u>

_	6	("5439833" "5640343" "6215140" "6339544" "6552926" "6597031"	USPAT	2004/09/07 12:27
_	2	"2003/0076703").PN. ("5363329" "5920788").PN.	USPAT	2004/09/07
_	3	("3206730" "3488636" "3201764").PN.	USPAT	2004/09/07
-	2	("5296716" "6087674" "2003/0186481" "2003/0206512").PN.	USPAT	2004/09/07 12:29
_	32	(ovonic or phase-changeable) and (transistor with array\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/07 12:45
_	7	(ovonic or phase-changeable) and (transistor near4 array\$1) and heat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/07 13:32
_	50	(ovonic or phase-changeable) and (switch\$3 with transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/07
-	9	<pre>(ovonic or phase-changeable) and (switch\$3 with transistor with heat\$3)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 13:34
_	4	("6191973" "6625054" "6673691" "6700813").PN.	USPAT	2004/09/07 13:35
-	49158	(heat\$3 or thermal) near5 cell\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/17
_	301	365/\$158,243,163.ccls. and (heat\$3 or thermal) near5 cell\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/08 15:42
-	24	365/\$158,243,163.ccls. and (heat\$3 or thermal) near5 cell\$3 with transistor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/08 15:50
-	26	365/158,243,163.ccls. and (heat\$3 or thermal) near5 cell\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/08 15:52
_	14	365/158,243,163.ccls. and (heat\$3 or thermal) near5 cell\$3 and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/08
_	15	365/158,243,163,113.ccls. and (heat\$3 or thermal) near5 cell\$3 and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/09 13:27
-	10	365/\$.ccls. and (heat\$3 or thermal) near5 drain near5 cell\$1 and transistor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/08 16:24
-	31	365/\$.ccls. and drain with (heat\$3 or thermal) near5 cell\$1 and transistor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/08 16:40

		dunin manna (hartea theresa)	HODE .	2004/00/00
-	3	drain near3 (heat\$3 or thermal) near5	USPAT;	2004/09/08
		cell\$1 and transistor\$1	US-PGPUB; EPO; JPO;	16:49
			DERWENT;	
			IBM TDB	
_	7	("4165642" "4734641" "5309090"	USPAT	2004/09/08
		"5414370" "5473259" "5886564"		16:42
		"5911897").PN.		
_	45	, , , , , , , , , , , , , , , , , , ,	USPAT;	2004/09/08
		cell\$1 and transistor\$1	US-PGPUB;	16:49
			EPO; JPO;	1
			DERWENT;	
	35	365/158,243,163,113,105,96,103,104,175.ccl	IBM_TDB	2004/09/09
-	35	and (heat\$3 or thermal) near5 cell\$3 and	US-PGPUB;	13:29
		transistor	EPO; JPO;	13.29
			DERWENT;	
			IBM TDB	
_	30	365/158,243,163,113,105,96,103,104,175.ccl		2004/09/09
		and (heat\$3 or thermal) near5 diode	US-PGPUB;	13:37
			EPO; JPO;	
			DERWENT;	
		0.65 /150 0.40 1.60 1.60 1.65 0.6 1.65 1.65 1.65	IBM_TDB	0004/00/15
-	10	365/158,243,163,113,105,96,103,104,175.ccl		2004/09/15
		and ((heat\$3 or thermal) near diode)	US-PGPUB; EPO; JPO;	09:35
			DERWENT;	
			IBM TDB	
_	1	365/158,243,163,113,105,96,103,104,175.ccl		2004/09/09
	-	and ((heat\$3 or thermal) near diode and	US-PGPUB;	13:50
		(zener adj diode\$1))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	365/\$.ccls. and ((heat\$3 or thermal) near	USPAT;	2004/09/09
		diode and (zener adj diode\$1))	US-PGPUB;	13:51
			EPO; JPO;	
			DERWENT; IBM TDB	
1_	118	((heat\$3 or thermal) near diode and	USPAT;	2004/09/09
1		(zener adj diode\$1))	US-PGPUB;	13:52
	l		EPO; JPO;	
1	1		DERWENT;	
			IBM_TDB	
-	75	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	USPAT;	2004/09/09
		(zener adj diode\$1)) and transistor	US-PGPUB;	13:52
	1		EPO; JPO;	
			DERWENT; IBM TDB	
_	1	365/158,243,163,113,105,96,103,104,175.ccl		2004/09/09
-		and ((heat\$3 or thermal) near diode and	US-PGPUB;	14:04
	1	(zener adj diode\$1))	EPO; JPO;	
		, , , , , , , , , , , , , ,	DERWENT;	
	}		IBM_TDB	
-	3	· · · · · · · · · · ·		2004/09/09
	l	and ((heat\$3 or thermal) near5 diode and	US-PGPUB;	14:07
	1	(zener adj diode\$1))	EPO; JPO;	
	1		DERWENT;	
1_	4	365/\$ cale and (/hoat\$3 on thormal)	<pre>IBM_TDB USPAT;</pre>	2004/09/09
-	4	365/\$.ccls. and ((heat\$3 or thermal) near5 diode and (zener adj diode\$1))	US-PGPUB;	14:11
		licars aroue and (zener ad) arodestill	EPO; JPO;	- 1 - 1 - 1
			DERWENT;	
			IBM TDB	
-	14	((heat\$3 or thermal) near5 diode and	USPĀT;	2004/09/09
	}	(zener adj diode\$1)) and (thermal adj	US-PGPUB;	14:16
		resistor)	EPO; JPO;	
1			DERWENT;	
	<u> </u>	<u> </u>	IBM_TDB	

-	9	((heat\$3 or thermal) near5 diode and	USPAT;	2004/09/09
	i	(zener adj diode\$1)) and (thermal adj	US-PGPUB;	14:16
1		resistor) and transistor	EPO; JPO;	
			DERWENT;	
,	ł		IBM TDB	
_	1	heat\$3 near4 switch\$3 near4 memory near4	USPAT;	2004/09/15
	_	diode	US-PGPUB;	08:59
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	7	365/\$.ccls. and heat\$3 same switch\$3 same	USPAT;	2004/09/15
	'	memory same diode	US-PGPUB;	09:12
	1	memory same drode	EPO; JPO;	05.12
			DERWENT;	
		1	IBM_TDB	2004/00/15
	9	heat\$3 with switch\$3 with memory with	USPAT;	2004/09/15
		diode	US-PGPUB;	09:13
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/00/55
-	104	heat\$3 same switch\$3 same memory same	USPAT;	2004/09/15
	·	diode	US-PGPUB;	09:15
			EPO; JPO;	
			DERWENT;	
]			IBM_TDB	
-	2	("4649333" "6002239").PN.	USPAT	2004/09/15
				09:23
-	30	365/158,243,163,113,105,96,103,104,175.ccl	sUSPAT;	2004/09/15
		and ((heat\$3 or thermal) near5 diode)	US-PGPUB;	09:36
			EPO; JPO;	į l
	1		DERWENT;	1
			IBM TDB	
_	1	365/158,243,163,113,105,96,103,104,175.ccl	sUSPAT;	2004/09/15
		and ((heat\$3 or thermal) near5 switch\$3	US-PGPUB;	09:37
		near5 memory near5 diode)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	3	365/158,243,163,113,105,96,103,104,175.ccl		2004/09/17
		and ((heat\$3 or thermal) same switch\$3	US-PGPUB;	11:31
	1	same memory same diode)	EPO; JPO;	
	1		DERWENT;	
	1		IBM TDB	
_	4	("3612758" "3681754" "5592409"	USPAT	2004/09/15
	"	(3812738 3881734 3392409 "5889694").PN.	551111	09:42
_	9	·	USPAT;	2004/09/15
_		switch\$3 same memory same diode)	US-PGPUB;	09:45
		switchips same memory same drode)	EPO; JPO;	05.45
	Į.		DERWENT;	
	1		· ·	
	122	//b-nt63 on thormal)	IBM_TDB	2004/09/15
-	130		USPAT;	2004/09/15
		memory same diode)	US-PGPUB;	09:45
			EPO; JPO;	
			DERWENT;	
	J		IBM_TDB	1